
CASE STUDY:
A Capacitive Accelerometer

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Thanks to SDS and Tim Dennison (ADI)

Outline

- > **Accelerometer fundamentals**
- > **Analog Devices accelerometer**
 - **History**
 - **Structure**
 - **Design and modeling**
 - **Fabrication and packaging**
 - **Noise and accuracy**

Measurement choices

- > **Two approaches to measuring acceleration**
 - **Open loop: Measure change due to acceleration**
 - **Closed loop: A disturbance in a position control system**

Accelerometer types

- > **Open vs. closed loop sensing**
 - **Open loop: Measure change due to acceleration**
 - **Closed loop: A disturbance in a position control system**

 - > **Quasi-static vs. resonant sensing**
 - **Quasi-static sensing**
 - » **Mechanical resonant frequency > Frequency of acceleration**
 - » **Measure displacement due to acceleration**
Optical, Capacitive, Piezoresistive, Tunneling
 - **Resonant sensing**
 - » **Measure change in resonant frequency**
Due to position-dependent nonlinear spring

 - > **Today's example involves a quasi-static accelerometer**
-

Accelerometer fundamentals

> Displacement and acceleration are coupled together by a fundamental scaling law

- A higher resonant frequency implies less displacement
 - » high f & low sensitivity
- Measuring small accelerations requires floppier structures
 - » high sensitivity and low f

$$x = \frac{F}{k} = \frac{ma}{k}$$

$$x = \frac{a}{\omega_0^2}$$

> Johnson noise in the damping mechanism gives rise to a fundamental noise floor for acceleration measurement

$$a_{n,rms} = \sqrt{\frac{4k_B T \omega_0}{mQ}}$$

Accelerometer specifications

- > Initial application arena was automotive crash sensor
- > Navigation sensors have tighter specs

<i>Parameter</i>	<i>Automotive</i>	<i>Navigation</i>
Range	±50g (airbag) ±2g (vehicle stability system)	±1g
Frequency Range	DC- 400Hz	DC-100Hz
Resolution	<100mg (airbag) <10mg (vehicle stability system)	<4μg
Off-axis Sensitivity	<5%	<0.1%
Nonlinearity	<2%	<0.1%
Max. Shock in 1msec	>2000g	>10g
Temperature Range	-40°C to 85°C	-40°C to 80°C
TC of Offset	<60mg/°C	<50 μg/°C
TC of Sensitivity	< 900ppm/°C	±50ppm/°C

Table 1 on p. 1642 in Yazdi, N., F. Ayazi, and K. Najafi. "Micromachined Inertial Sensors." *Proceedings of the IEEE* 86, no. 8 (August 1998): 1640-1659. © 1998 IEEE.

Piezoresistive accelerometers

- > Use piezoresistors to convert stress in suspension beam \rightarrow change in resistance \rightarrow change in voltage
- > First MEMS accelerometer used piezoresistors
 - Roylance and Angell, IEEE-TED ED26:1911, 1979
 - Bulk micromachined
 - Glass capping wafers to damp and stop motion
- > Simple electronics
- > Piezoresistors generally less sensitive than capacitive detection

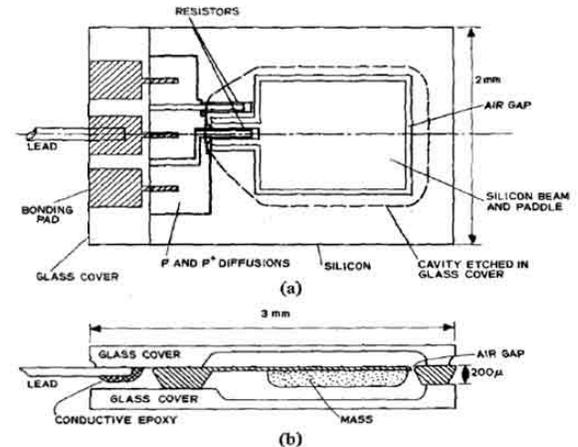


Fig. 1. Top and cross-section views of the accelerometer. (a) Top view. (b) Centerline cross section.

Figure 1 on p. 1911 in Roylance, L. M., and J. B. Angell. "A Batch-fabricated Silicon Accelerometer." *IEEE Transactions on Electron Devices* 26, no. 12 (December 1979): 1911-1917. © 1979 IEEE.

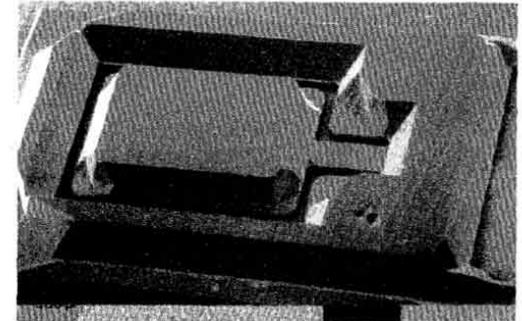


Fig. 2. SEM of backside of the accelerometer with a silicon mass after KOH etch.

Figure 2 on p. 1911 in Roylance, L. M., and J. B. Angell. "A Batch-fabricated Silicon Accelerometer." *IEEE Transactions on Electron Devices* 26, no. 12 (December 1979): 1911-1917. © 1979 IEEE.

Capacitors for position measurement

> Single capacitors

- Capacitance is function of gap or area
- Can be nonlinear

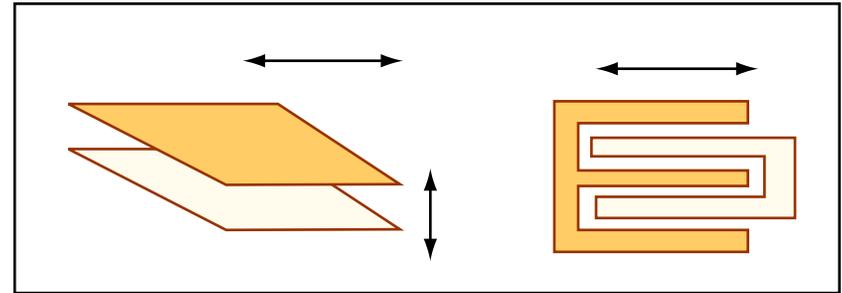


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Adapted from Figure 19.3 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 501. ISBN: 9780792372462.

> Differential capacitors

- One capacitor increases while the other decreases

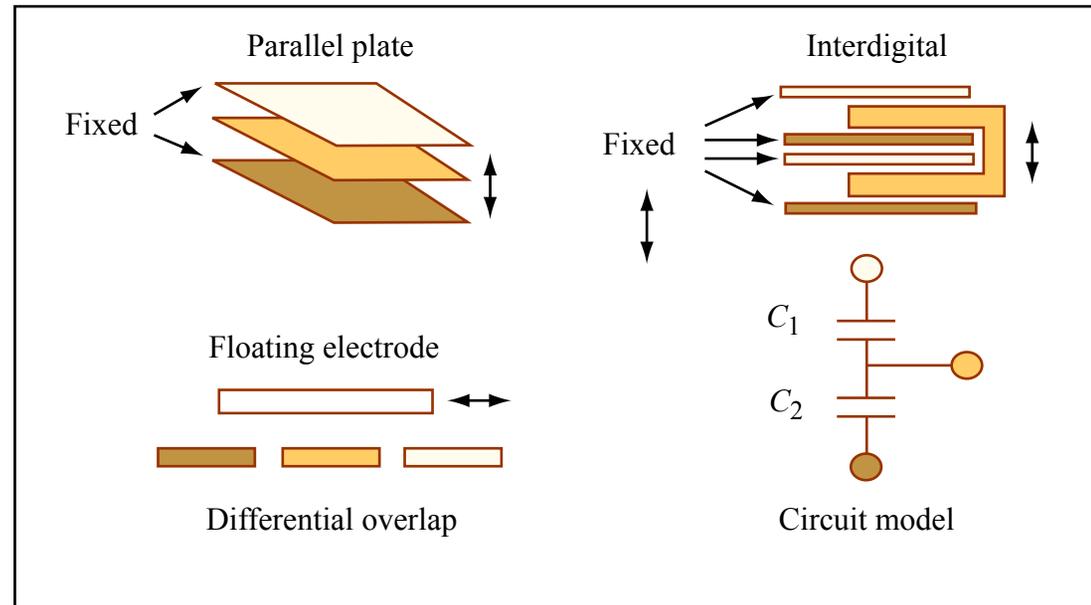


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Adapted from Figure 19.4 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 501. ISBN: 9780792372462.

Using a differential capacitor

- > Differential drive creates sense signal proportional to capacitance difference
- > Gives zero output for zero change
- > Output linear with gap

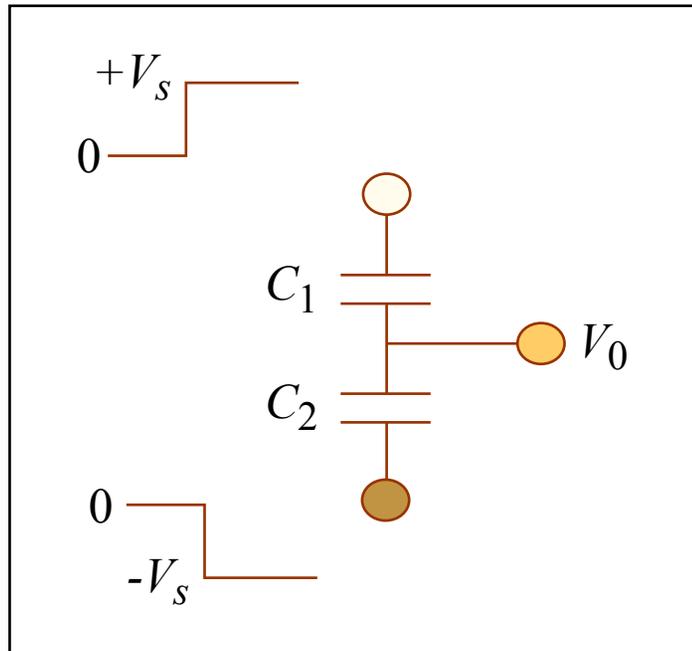


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Adapted from Figure 19.5 in Senturia, Stephen D. *Microsystem Design*.
Boston, MA: Kluwer Academic Publishers, 2001, p. 502. ISBN: 9780792372462.

$$V_0 = -V_s + \frac{C_1}{C_1 + C_2} (2V_s) = \frac{C_1 - C_2}{C_1 + C_2} V_s$$

for parallel-plate capacitors where
only g changes, this becomes

$$V_0 = \frac{g_2 - g_1}{g_1 + g_2} V_s$$

Bulk-micromachined capacitive accelerometer

> Fabrication not reported, but likely uses nested-mask process

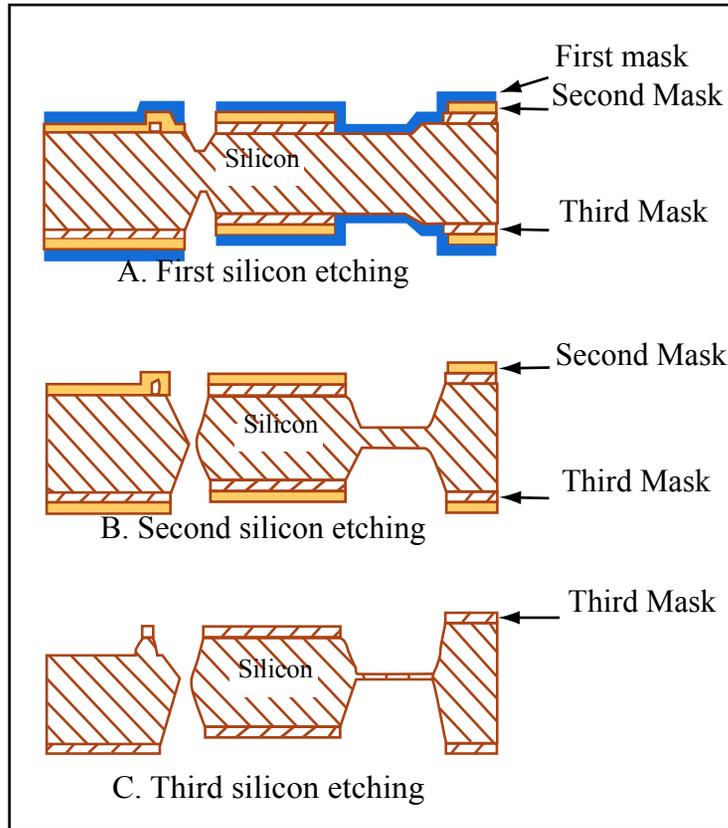


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Adapted from Figure 3 on p. 688 in Sasayama, T., S. Suzuki, S. Tsuchitai, A. Koide, M. Suzuki, T. Nakazawa, and N. Ichikawa. "Highly Reliable Silicon Micro-machined Physical Sensors In Mass Production." *The 8th International Conference on Solid-State Sensors and Actuators and Eurosensors IX: digest of technical papers. June 25-29, 1995, Stockholm, Sweden.* Stockholm, Sweden: Foundation for Sensor and Actuator Technology, 1995, pp. 687-690. ISBN: 9789163034732. Figure originally from Koide, A., K. Sato, S. Suzuki, and M. Miki. *Technical Digest of the 11th Sensor Symposium: June 4-5, 1992, Arcadia Ichigaya, Tokyo.* Tokyo, Japan: Institute of Electrical Engineers of Japan, 1992, pp. 23-26.

Cite as: Joel Voldman, course materials for 6.777J / 2.372J Design and Fabrication of Microelectromechanical Devices, Spring 2007. MIT OpenCourseWare (<http://ocw.mit.edu/>), Massachusetts Institute of Technology. Downloaded on [DD Month YYYY].

Thermal accelerometer

- > **MEMSIC thermal convection accelerometer**
- > **Gas is proof mass**
- > **Movement of gas under acceleration changes thermal profile**

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Transimpedance circuits

- > The simplest type of circuit measures the displacement current in a capacitor using a transimpedance amplifier
 - Transimpedance converts current to voltage
 - Nulls out parasitic capacitance
- > If source is DC, measure velocity of motion

> Velocity is not really what we want...

$$Q = C(x, t)V_c$$

$$v_- \approx v_+ = 0 \Rightarrow V_c = V_s$$

$$i_c = \frac{dQ}{dt} = C(x, t) \frac{dV_s}{dt} + V_s \left. \frac{\partial C}{\partial x} \right|_{V_s} \frac{dx}{dt}$$

$$i_c = V_s \left. \frac{\partial C}{\partial x} \right|_{V_s} \frac{dx}{dt} = -\frac{V_0}{R_F}$$

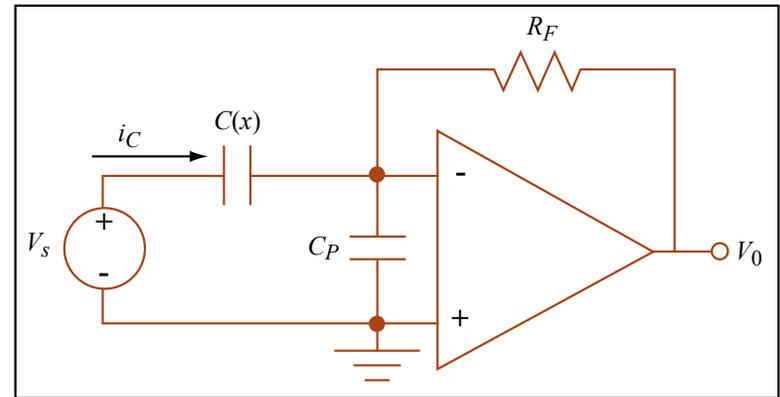


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Adapted from Figure 19.6 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 503. ISBN: 9780792372462.

$$V_0 = \underbrace{-R_F V_s \left. \frac{\partial C}{\partial x} \right|_{V_s}}_{\text{constant}} \frac{dx}{dt}$$

Transimpedance circuits

- > If source is AC, can measure position
- > First, must use frequency high enough such that velocity term is negligible
- > Second, operate above corner frequency of LP filter

$$i_c = \frac{dQ}{dt} = C(x, t) \frac{dV_c}{dt} + V_c \left. \frac{\partial C}{\partial x} \right|_{V_c} \frac{dx}{dt}$$

$$V_s = V_{s0} \cos(\omega t) = \text{Re} \{ V_{s0} e^{j\omega t} \}$$

$$i_c = \left[C(x, t) j\omega + \left. \frac{\partial C}{\partial x} \right|_{V_c} \frac{dx}{dt} \right] V_s$$

$$i_c \approx C(x, t) j\omega V_s$$

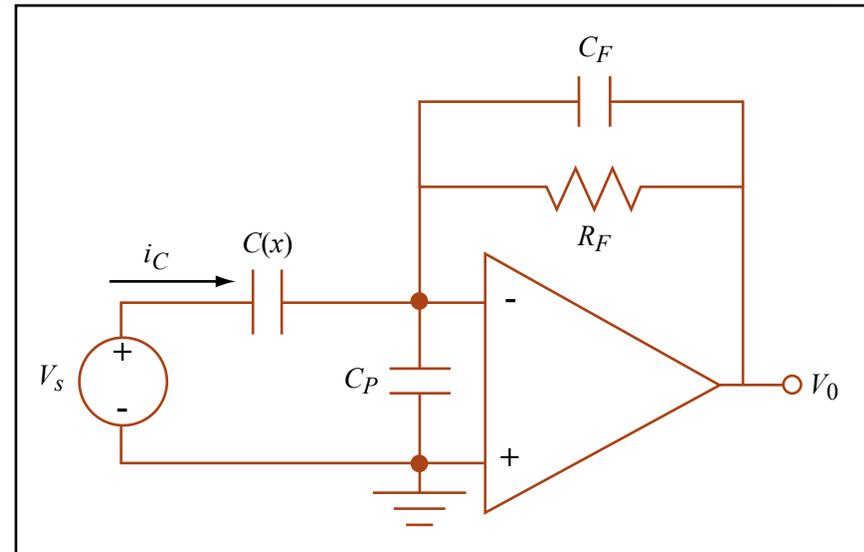


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Adapted from Figure 19.7 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 504. ISBN: 9780792372462.

$$V_0 = -i_c (C_F \parallel R_F) = -i_c \frac{R_F}{1 + j\omega C_F R_F}$$

$$V_0 \approx \frac{-i_c R_F}{j\omega C_F R_F} = \frac{-i_c}{j\omega C_F} \approx \frac{-C(x, t) j\omega V_s}{j\omega C_F}$$

$$V_0 \approx -\frac{C(x, t)}{C_F} V_s$$

Non-inverting op-amp circuits

> Now there is no virtual ground and parasitic capacitance appears in output

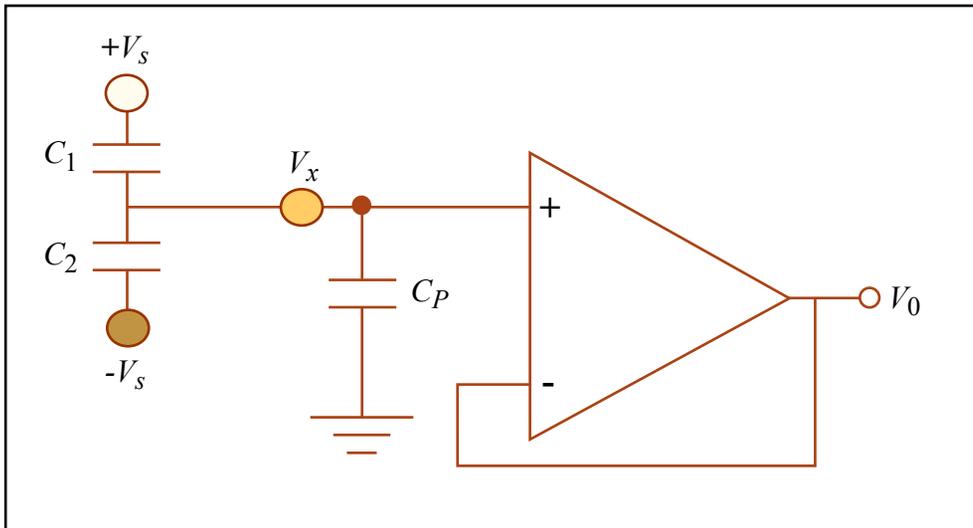


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Adapted from Figure 19.9 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 506. ISBN: 9780792372462.

$$V_0 = V_x = \frac{C_1 - C_2}{C_1 + C_2 + C_P} V_s$$

AC Methods Require Demodulation

> For AC methods, output signal is a HF sinusoid (carrier) multiplied by a LF signal

$$V_0 \approx -\frac{C(x,t)}{C_F} V_S(t)$$

> This is an amplitude-modulated (AM) signal

> We want to retrieve the low-frequency component

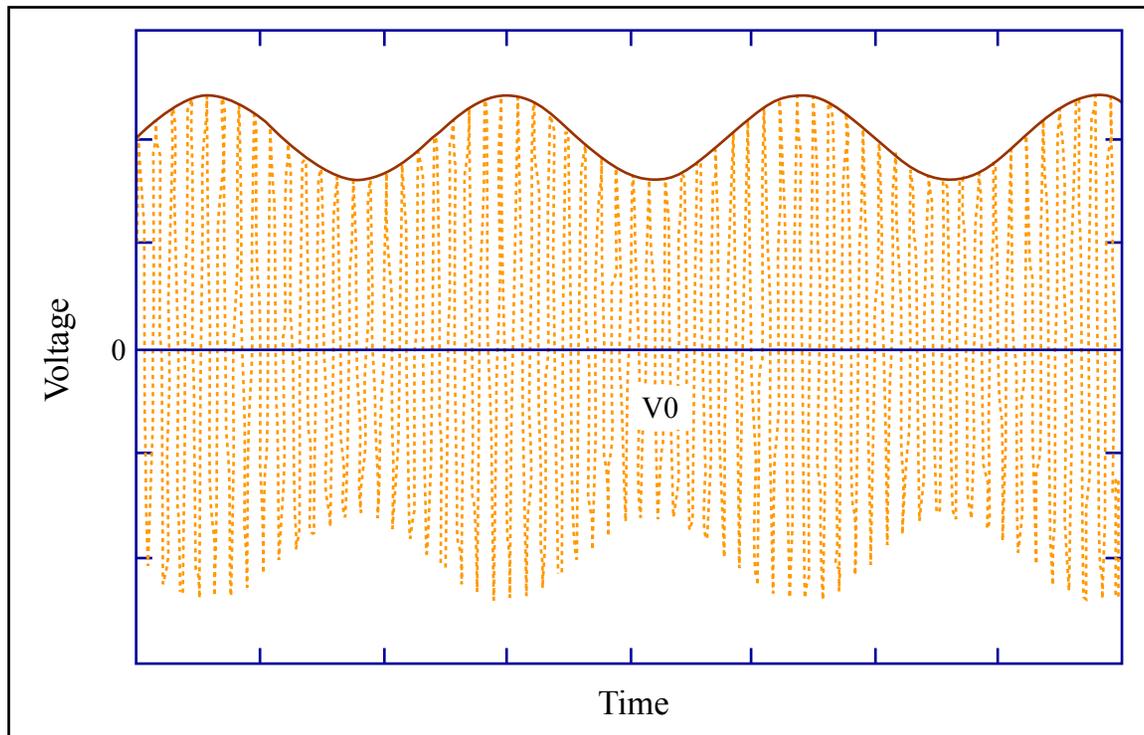


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Adapted from Figure 19.11 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 508. ISBN: 9780792372462.

Synchronous Demodulation

- > Use a nonlinear circuit to multiply V_0 by an in-phase sinusoid
- > This demodulates to baseband
- > Relative phase is important

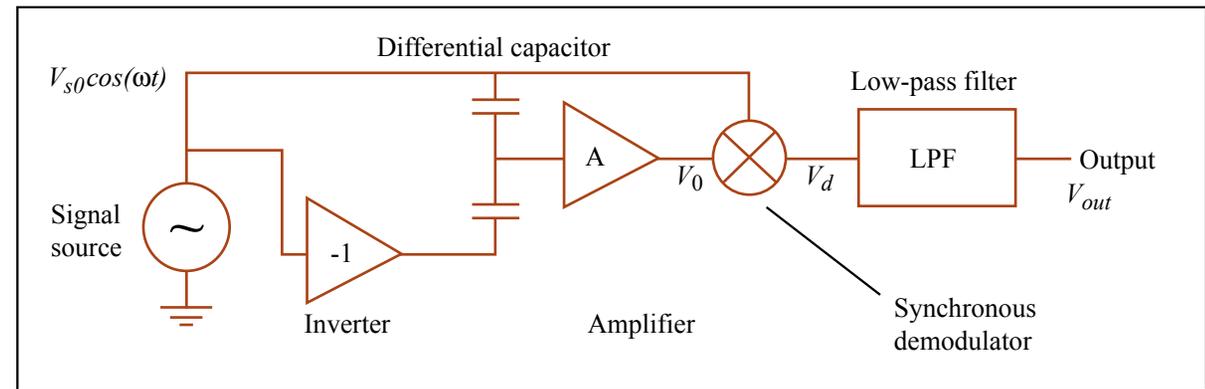


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$$V_0 \approx -\frac{C(x,t)}{C_F} V_S$$

$$V_0 \approx -\frac{C(x,t)}{C_F} V_{S0} \cos(\omega t)$$

$$V_d = V_0 \cdot V_s = V_0 \cdot V_{s0} \cos(\omega t + \theta)$$

Allow phase shift

$$V_d = -\frac{C(x,t)}{2C_F} V_{s0}^2 [\cos(\theta) + \cos(2\omega t + \theta)]$$

$$V_{out} = -\frac{C(x,t)}{2C_F} V_{s0}^2 \cos(\theta)$$

Signal-to-noise Issues

> To get a big signal, use a big voltage

— BUT —

$$V_0 \approx -\frac{C(x,t)}{C_F} V_S(t)$$

Voltage creates a force that can modify the state of the mechanical system (analogous to the self-heating problem in resistance measurement)

> Noise floor *minimum* often set by LPF bandwidth

> But amplifier noise will often dominate

Analog Devices accelerometer

- > Genesis: An ADI engineer heard about forming mechanical sensors on silicon**
- > Market pull was airbag accelerometers (50g)**
 - Current product was \$50
 - Auto manufacturers wanted \$5 price point
- > Team was formed in 1986, first product in 1993**
 - Fabrication process was under development since early 80's at Berkeley

Analog Devices accelerometer

- > Initially partitioned system to *integrate* electronics on-chip
 - This ensured that they could achieve good SNR
- > BUT
 - Entailed large infrastructure costs that essentially hemmed future opportunities
- > This is an example where up-front system partitioning has *multi-decade* consequences

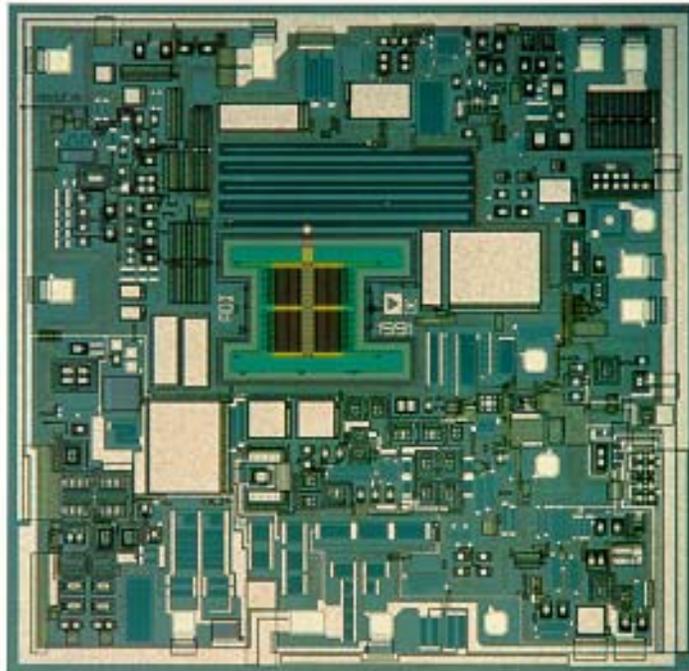
ADI system partitioning

- > **How to integrate MEMS + circuits?**
- > **Circuits typically are run on continually changing (and improving) fabrication lines**
- > **MEMS typically cannot economically support such high throughputs**
- > **Foundries will not accept non-pristine wafers**
- > **Thus, must combine both in-house in a dedicated foundry**
 - **This usually sets circuit technology**
 - **For ADI, foundry is in Cambridge and Limerick**

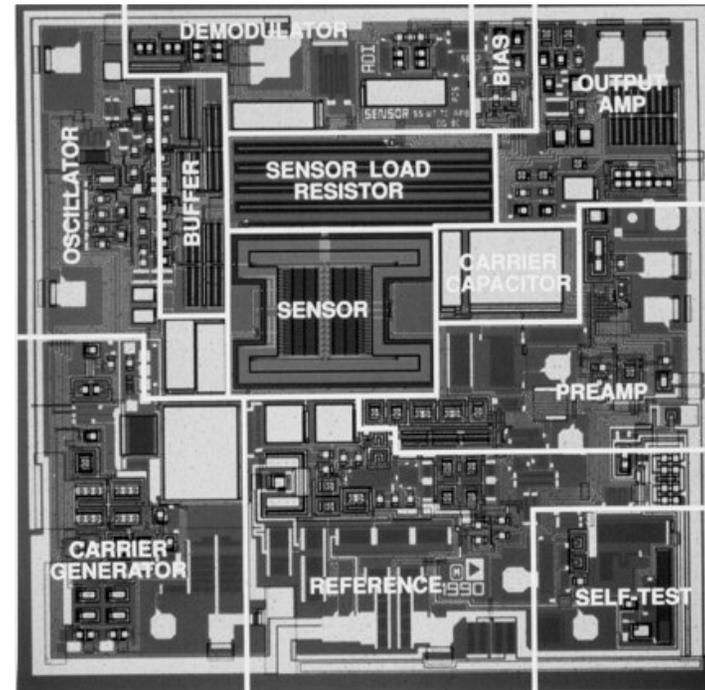
ADI system partitioning

- > **How to integrate MEMS + circuits?**
- > **Several different approaches**
 - **MEMS first**
 - **Circuits first**
 - **MEMS in the middle**
- > **ADI chose MEMS-in-the-middle**
 - **Mostly developed at Berkeley**
 - **6" fab line**
 - **~1 million sensors/week (as of 2005)**

Analog Devices ADXL50



XL50



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Differential capacitor structure

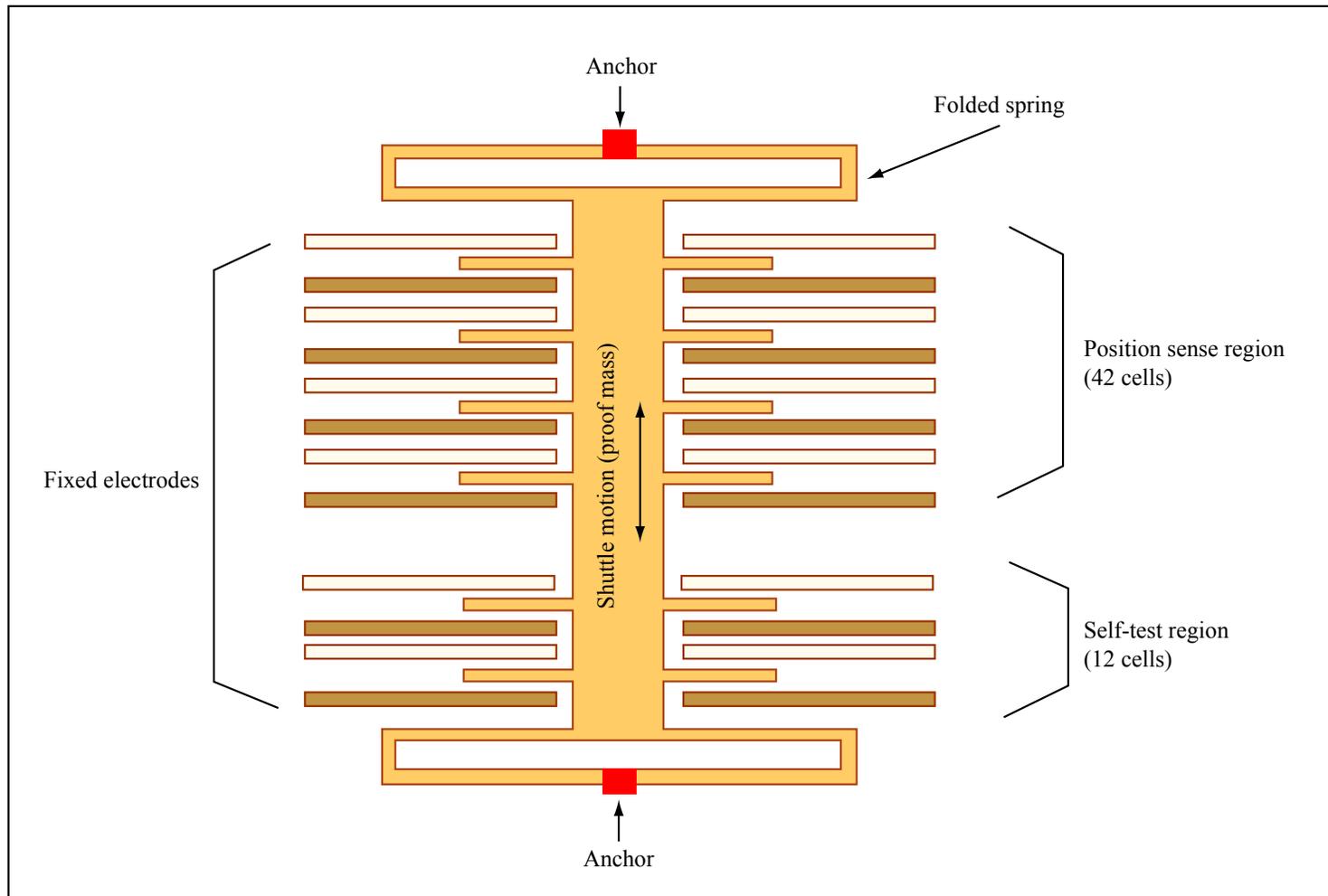


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Closer views

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Even closer

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Fabrication sequence

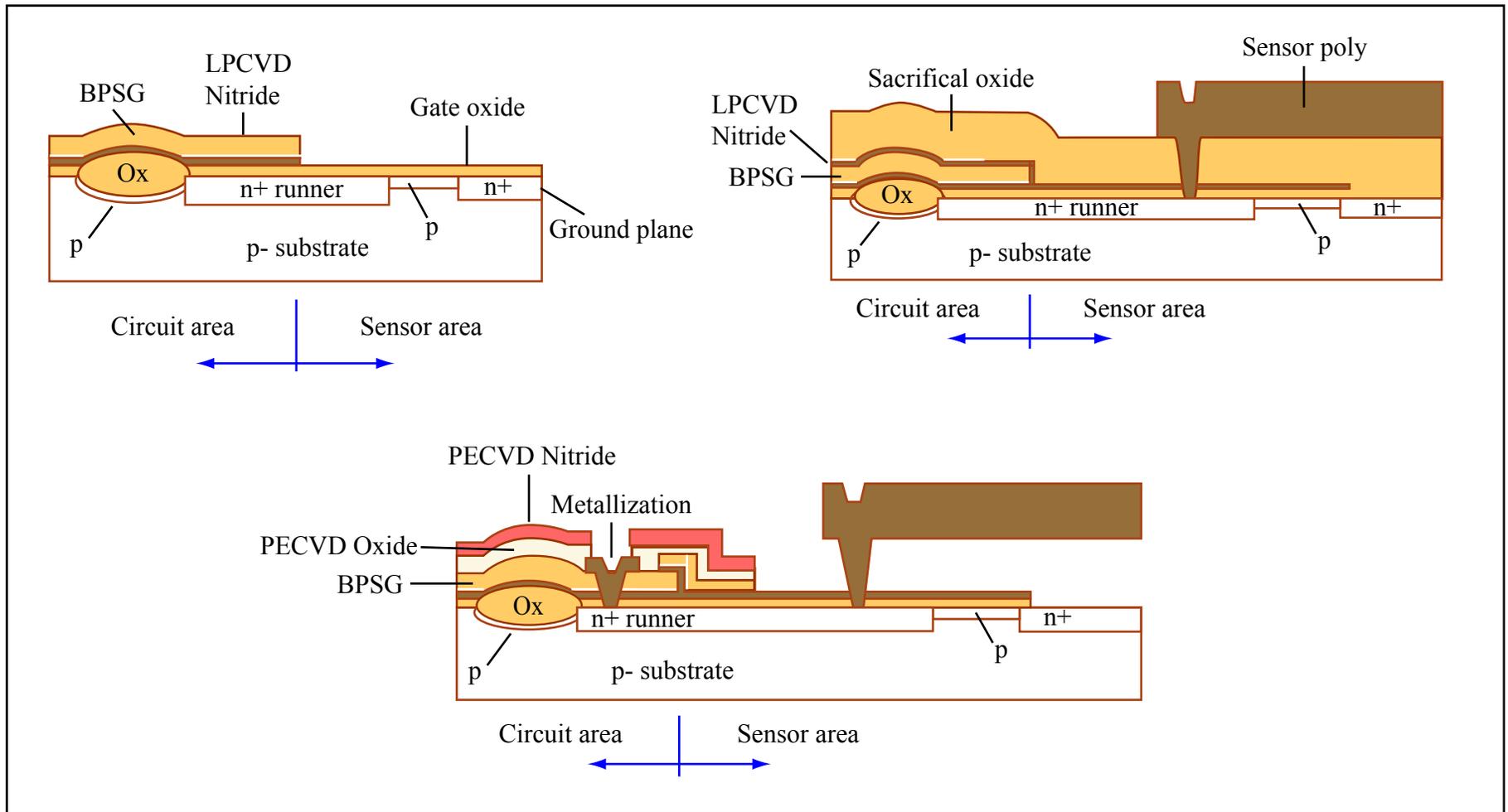
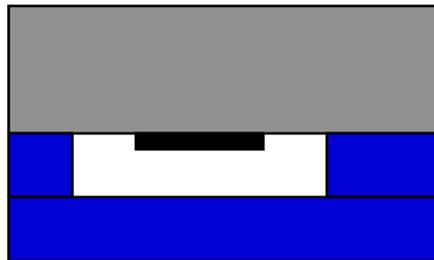


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Adapted from Figures 19.23, 19.24, and 19.26 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, pp. 521 and 523. ISBN: 9780792372462.

Packaging

- > When to do die saw, before or after release?
- > ADI decided to do die separation after release and invented a wafer-handling method to protect the released region during sawing
 - One tape layer with holes corresponding to mechanical region
 - A second tape layer covering the entire chip
 - Saw from the back (must have pre-positioned alignment marks on wafer back to do this)



Packaging

> Processing issues

- Stiction at- and post-release
 - » Solved at-release stiction with bumps under poly structures
 - » Post-release stiction avoided with proprietary coating
 - Thermally evaporated silicone coating
 - Has to withstand packaging temps

> Laser trimming

- Set offsets, slopes, etc.
- At wafer scale
- Before packaging...

System diagram

- > Oscillator provides AC waveform for sensing
- > Waveforms:

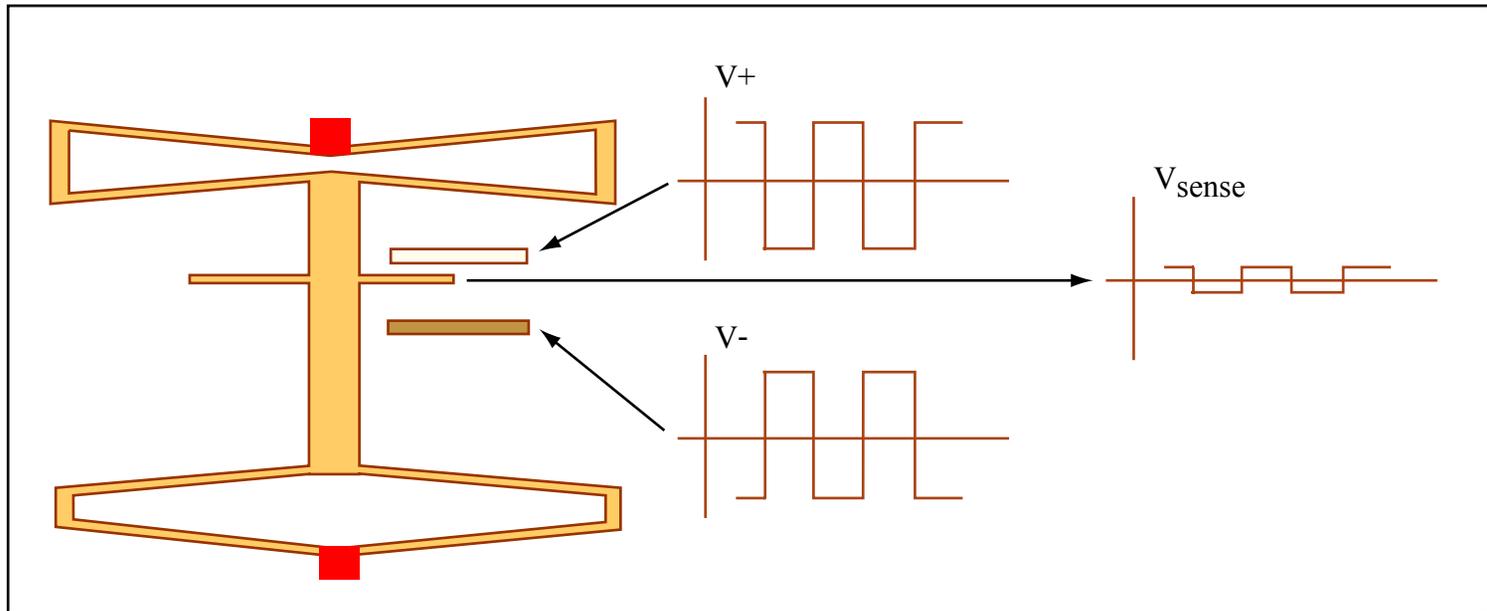


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Adapted from Figure 19.21 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 516. ISBN: 9780792372462.

Stiffness of springs

$$C_{sense} \approx 42 \frac{\epsilon_0 H L_0}{g_0 \pm y} \approx 60 \text{fF} \left[1 \pm \frac{y}{g_0} \right]$$

> Parallel-plate approximation to sense capacitance is off by about 50%

> Beam bending model gives good estimate of stiffness

$$k \cong 2 \frac{\pi^4}{6} \left[\frac{EWH^3}{(2L_1)^3 + (2L_2)^3} \right] \cong 5.6 \text{ N/m}$$

$$\omega_0 = 24.7 \text{ kHz}$$

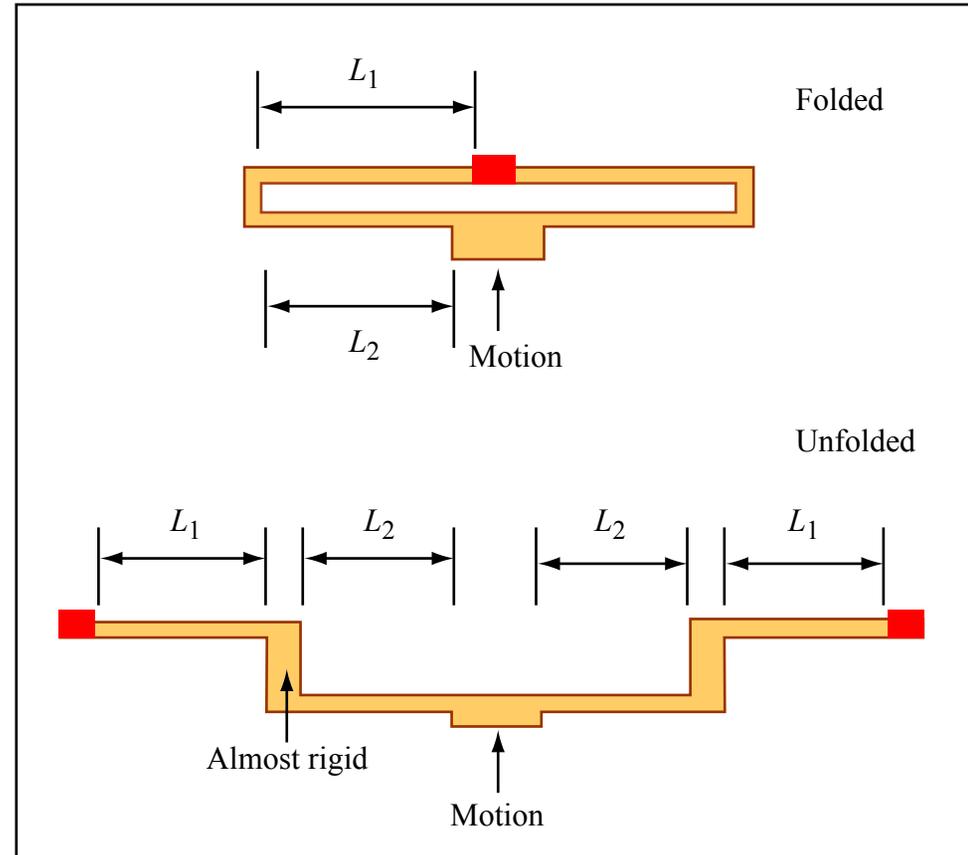
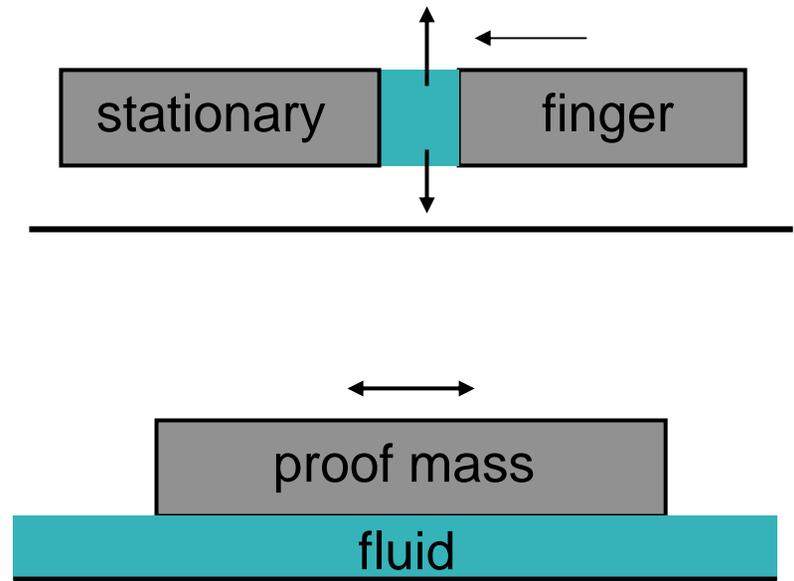


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Adapted from Figure 19.22 in Senturia, Stephen D. *Microsystem Design*. Boston, MA: Kluwer Academic Publishers, 2001, p. 518. ISBN: 9780792372462.

Design and modeling

- > Q of mechanical resonance is 5
 - Extremely hard to model accurately
 - Squeezed film damping between fingers
 - Couette drag beneath proof mass
 - Complex actual geometry
 - Rough model gives $Q = 34$, a poor estimate



ADXL50

- > First accelerometer used feedback control to keep plates fixed
- > Let's use PD control to see what it affects $K(s) = K_0(1 + \gamma s)$
- > Input is disturbance $D(s)$ – acceleration
- > Output is force from controller $F(s)$
- > $H(s)$ is accelerometer: SMD

$$\frac{F(s)}{D(s)} = -\frac{HK}{1+HK} = \frac{-\frac{K_0}{m}(1+\gamma s)}{s^2 + \left(\frac{b}{m} + \gamma \frac{K_0}{m}\right)s + \frac{k+K_0}{m}}$$

ADXL50

> Use feedback to get both

- Critical damping (when ON)
- Insensitivity to material properties

$$\frac{F(s)}{D(s)} = \frac{-\frac{K_0}{m}(1 + \gamma s)}{s^2 + \left(\frac{b}{m} + \gamma \frac{K_0}{m}\right)s + \frac{k + K_0}{m}}$$

> Choose $K_0 \gg k$

- ADI chose 10x

$$\left(\frac{b}{m} + \gamma \frac{K_0}{m}\right)^2 = 4 \left(\frac{k + K_0}{m}\right)$$

> Critical damping is when $b^2 = 4ac$ ($Q_{\text{closed-loop}} = 1/2$)

- Can pick K_0 and γ to meet both requirements

$$\left(\frac{b}{m} + \gamma \frac{K_0}{m}\right) \approx 2\sqrt{\frac{K_0}{m}}$$

$$\left(\frac{\omega_0}{Q_{o.l.}} + \gamma \frac{K_0}{m}\right) \approx 2\sqrt{\frac{K_0}{m}}$$

> Sensor response will be insensitive to changes in k

$$\gamma \frac{K_0}{m} \approx 2\sqrt{\frac{K_0}{m}} - \frac{1}{Q_{o.l.}} \sqrt{\frac{k}{m}} \approx 2\sqrt{\frac{K_0}{m}}$$

$$\gamma \approx 2\sqrt{\frac{m}{K_0}}$$

The next generations

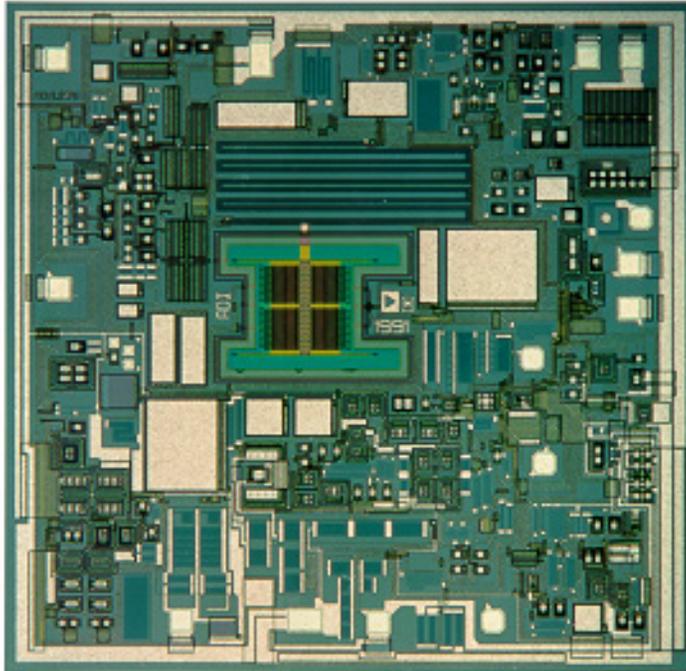
> In the next generation, ADI abandoned feedback

> Why?

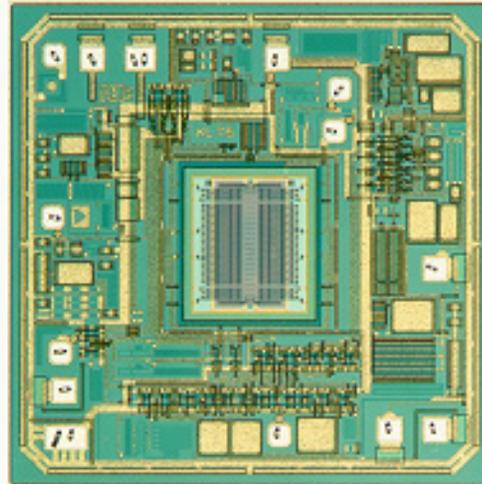
- **After years of testing, ADI found that polySi was structurally stable for intended markets**
- **Feedback required extra electronics → bigger chip → \$\$**
- **Needed external capacitor to set LPF**
 - » **Extra cost, extra complexity**
- **Closed-loop design was not ratiometric to power supply**
 - » **Customers needed to measure supply voltage**
- **DC bias at fingers for force feedback caused charges to move and thus devices to drift**

> Therefore, they removed feedback

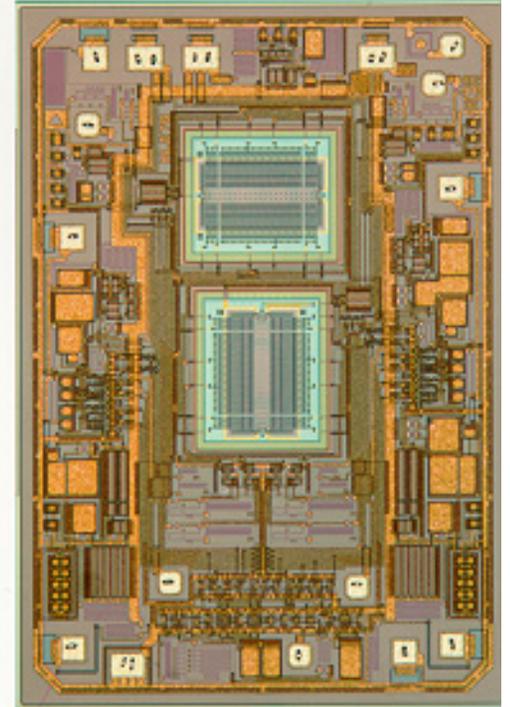
Analog Devices Dies shots



XL50



XL76



XL276

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Next generation specifications

- > Text study is of ADXL150 (XL76)
- > Text lists 22 specifications, covering sensitivity, range, temperature range, supply voltage, nonlinearity, cross-axis response, bandwidth, clock noise, drop test, shock survival, etc etc.
- > Also, response is *ratiometric*, proportional to the supply voltage
- > Sensitivity is $\beta V_s = 38 \text{ mV/g}$

$$V_{out} = \frac{V_s}{2} \pm \alpha + a\beta V_s$$

↑
offset

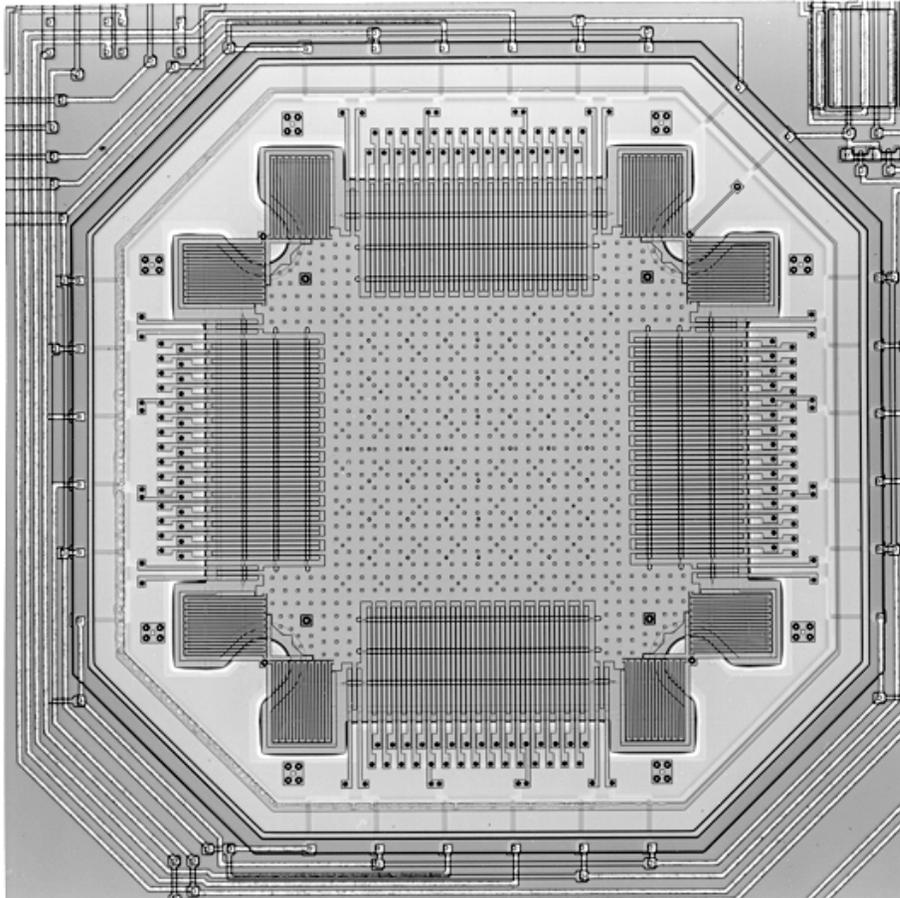
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Noise and accuracy

- > Noise is specified as $1 \text{ mg/Hz}^{1/2}$ in a bandwidth from 10 Hz to 1000 Hz
- > Corresponding Brownian noise estimate is half that value, corresponding to a rms position noise of 0.013 nm
- > Offset errors
 - If device is not perfectly balanced at zero g, turning on voltage aggravates the offset
 - Accurate etching required special “dummy” features to ensure that all cuts had the same profile (we have seen similar effects when we looked at DRIE)
- > Cross-axis sensitivity is low because of squeeze-film damping and differential capacitor measurement

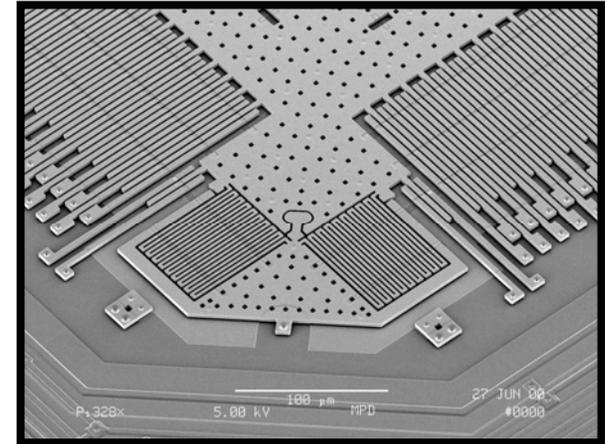
ADXL202 2-axis accelerometer

> Then moved from two 1-axis sensors to one 2-axis

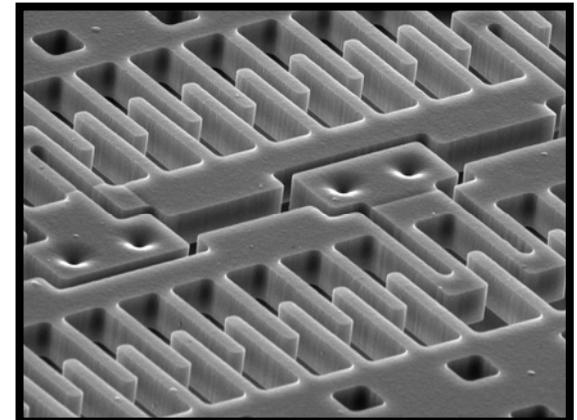


ADXL202 Sensor Structure

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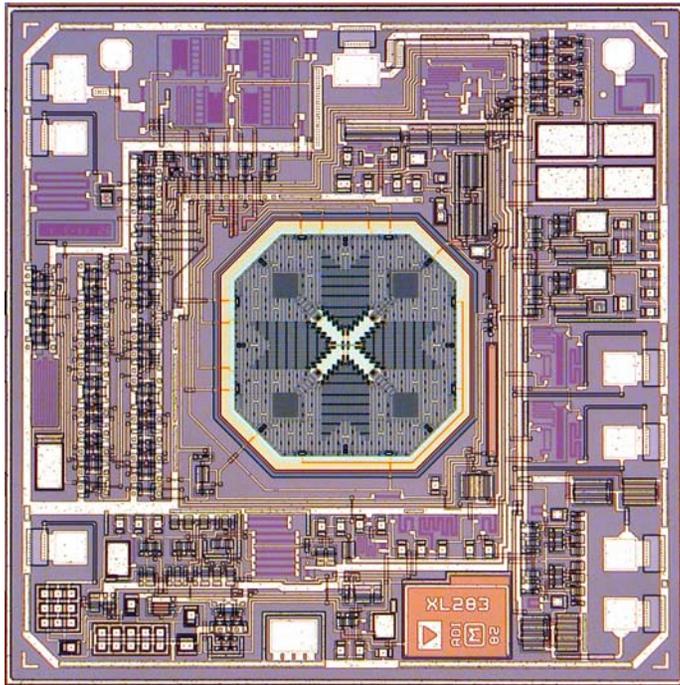
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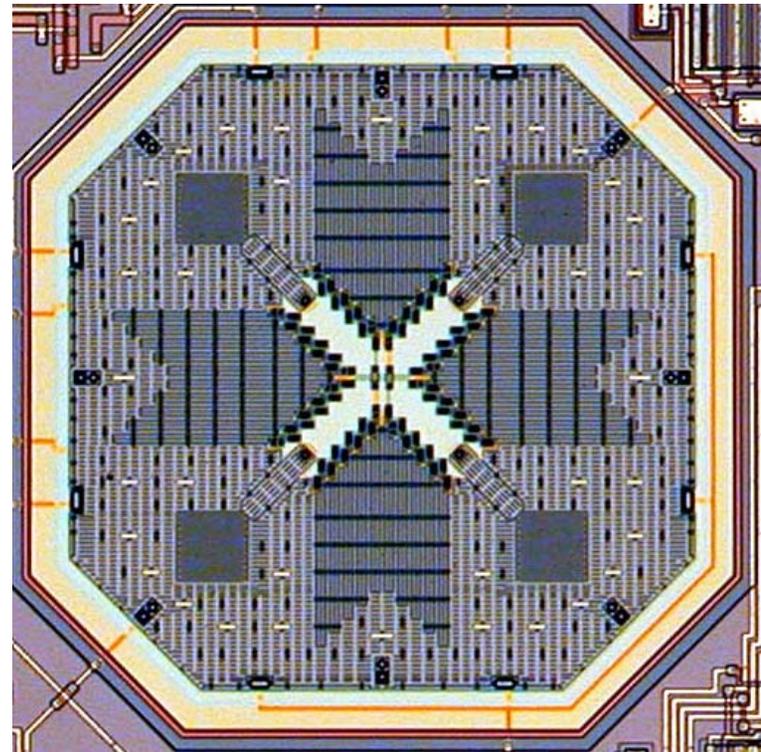
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Newer designs

- > ADXL203 two-axis accelerometer
- > Supports are in center of die to cancel 1st-order stresses due to packaging



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The latest design: ADXL40

> The newest designs use an SOI-MEMS process

- Also developed at Berkeley

> Enables several circuit features

- 0.6 μm CMOS allows 10x more transistors in same size
- Allows poly fuse trims to be set on-chip

» Can trim AFTER packaging

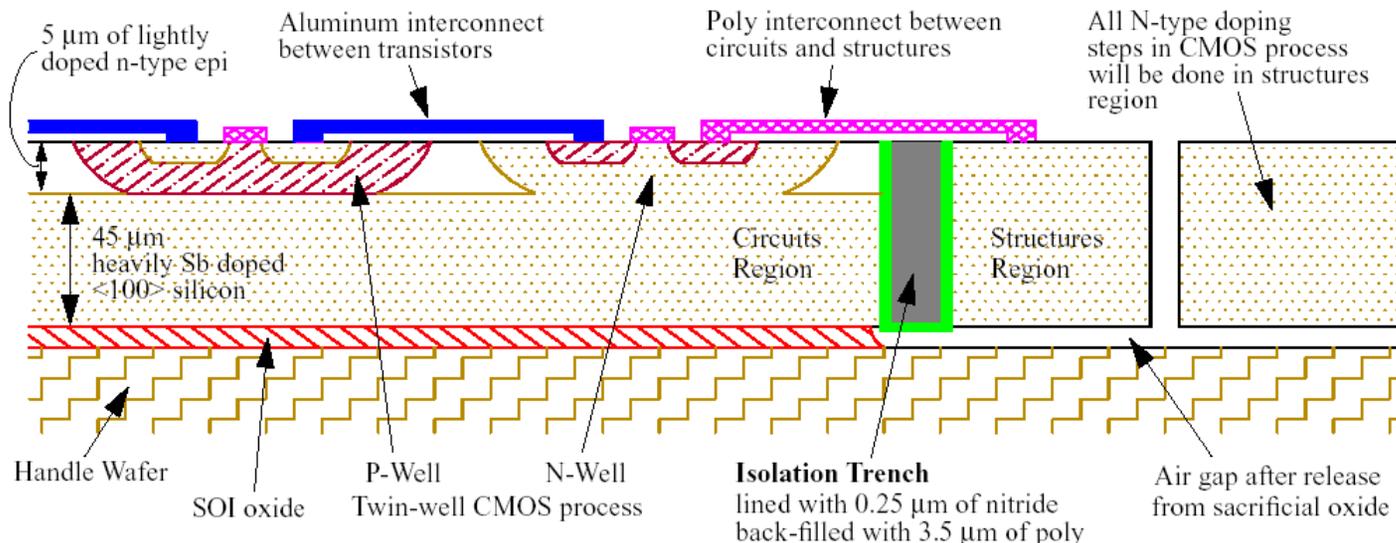


Figure 1 on p. 637 in Brosnihan, T. J., J. M. Bustillo, A. P. Pisano, and R. T. Howe. "Embedded Interconnect and Electrical Isolation for High-aspect-ratio, SOI Inertial Instruments." In *Transducers '97 Chicago: 1997 International Conference on Solid State Sensors and Actuators: digest of technical papers, June 16-19, 1997*. Vol. 1. Piscataway, NJ: IEEE, 1997, pp. 637-640. ISBN: 9780780338296. © 1997 IEEE.

The latest design: ADXL40

> MEMS

- Higher-aspect ratio structures lead to more squeezed-film damping $\rightarrow Q=1$
- Trench isolation allows self-test to be electrically isolated from sensing fingers
 - » Allows 2x voltage applied \rightarrow 4x force

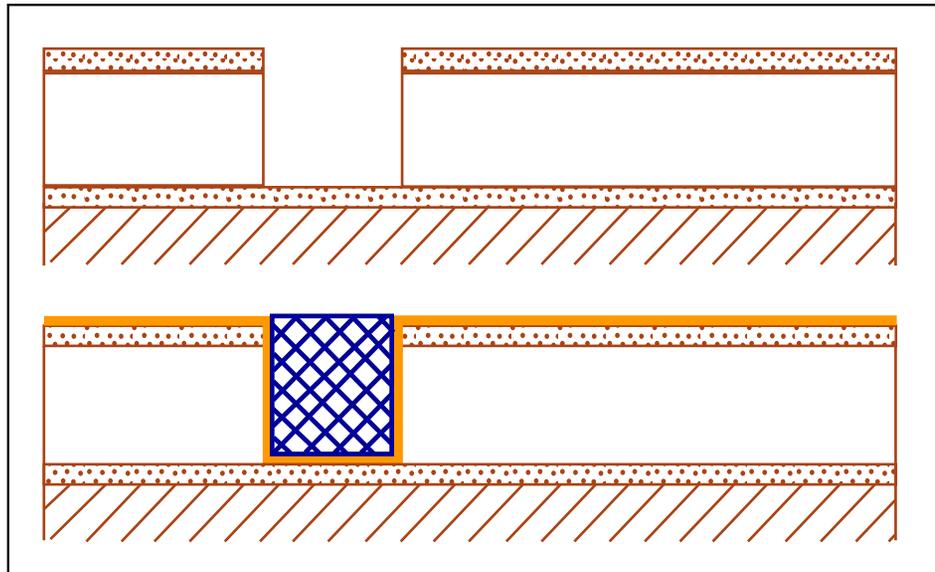


Image by MIT OpenCourseWare.

ADXL40

> Die shots

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New accelerometer markets

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Summary

- > Accelerometers are a MEMS success story**
- > Early system partitioning decisions have had profound downstream effects**
 - Eases sensor design and sensing**
 - Requires large internal infrastructure**
 - » And can never go to TSMC...**